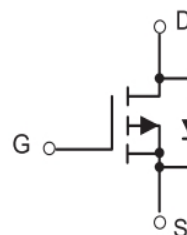


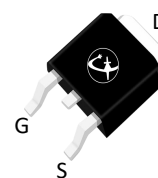
MAIN CHARACTERISTICS

I_D	-30 A
V_{DSS}	-60 V
$R_{DS(on)-typ}$ (@ $V_{GS}=-10V$) $T_C=25^{\circ}C$)	23.5m Ω



FEATURES

- Low gate charge
- Low C_{rss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-252

APPLICATIONS

- Brushless motor
- Load switch
- Uninterruptible power supply

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275 $^{\circ}C$ maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LT30P06AD	TO-252	LT30P06AD	Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continue Drain Current	I_D	-30	A
Pulsed Drain Current (Note1)	I_{DM}	-120	A
Single Pulsed Avalanche Energy	E_{AS}	100	mJ
Power Dissipation	P_D	85	W
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.43	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	BV_{DSS}	-60	-	-	V
Drain-Source Leakage Current	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	-1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	$V_{GS(th)}$	-1	-	-2.2	V
Drain-Source On-State Resistance	$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	$R_{DS(on)}$	-	23.5	30	m Ω
	$V_{GS} = -4.5 \text{ V}, I_D = -15 \text{ A}$		-	27	36	m Ω
Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	C_{iss}	-	2726	-	pF
Output Capacitance		C_{oss}	-	176	-	pF
Reverse Transfer Capacitance		C_{rss}	-	144	-	pF
Turn-on Delay Time(Note2)	$V_{DS} = -40 \text{ V}, V_{GS} = -10 \text{ V}, R_G = 5 \Omega, I_D = -20 \text{ A}$	$t_{d(ON)}$	-	11	-	ns
Rise Time(Note2)		t_r	-	59	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	116	-	ns
Fall Time(Note2)		t_f	-	66	-	ns
Total Gate Charge(Note2)	$V_{DS} = -40 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	Q_G	-	68	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	5.6	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	22	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	-30	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	-120	A
Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -20 \text{ A}, T_J = 25$	V_{SD}	-	-	-1.2	V
Reverse Recovery Time(Note2)	$I_{SD} = -20 \text{ A}, V_{GS} = 0 \text{ V}, dI_F / dt = 100 \text{ A}/\mu\text{s}$	t_{rr}	-	27	-	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	60	-	nC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

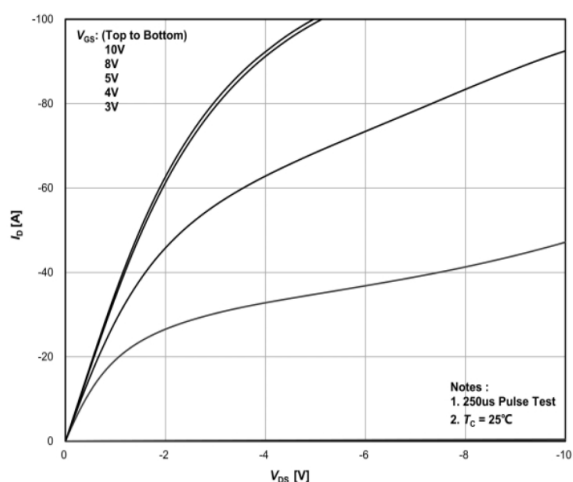


Figure 1. On-Region Characteristics

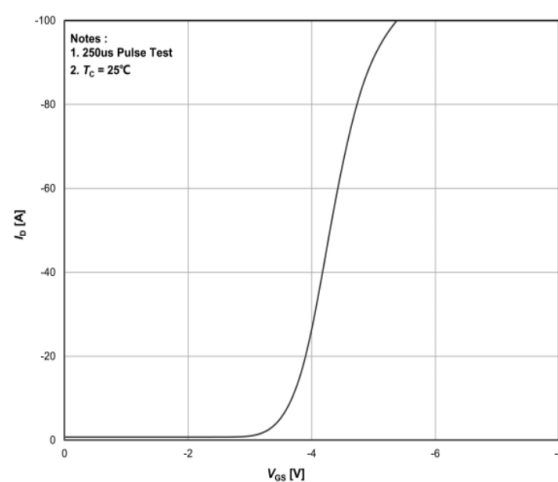


Figure 2. Transfer Characteristics

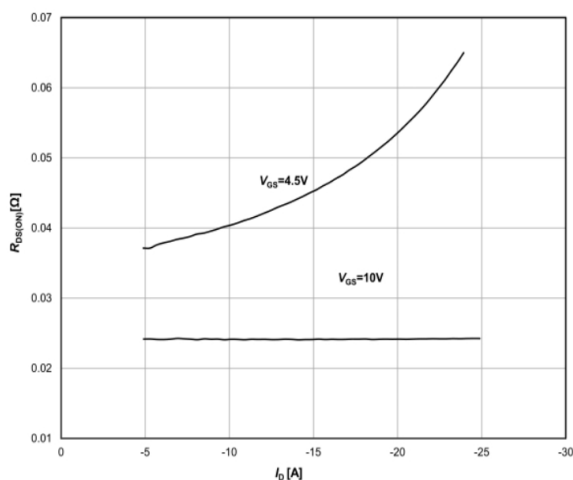


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

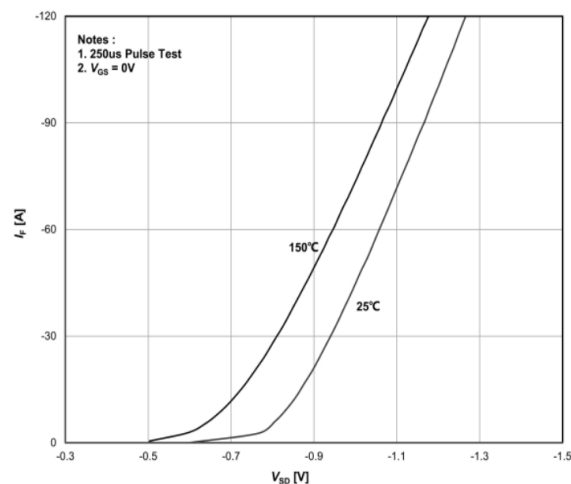


Figure 4. Body Diode Forward Voltage Variation with Current

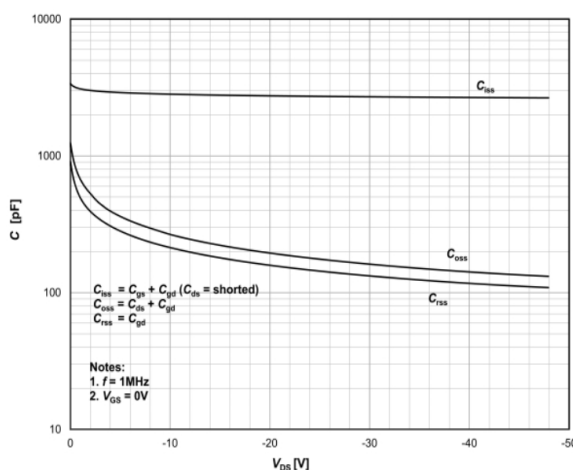


Figure 5. Capacitance Characteristics

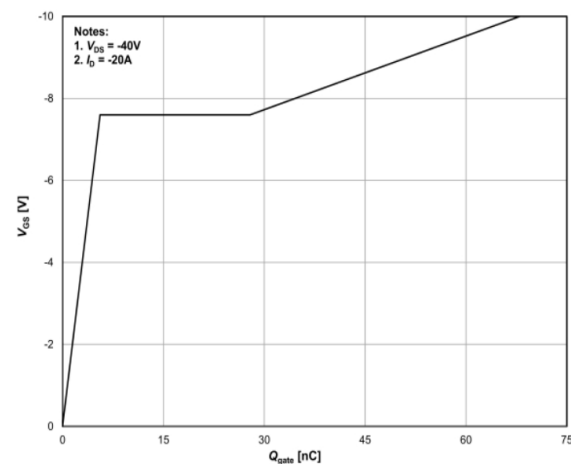


Figure 6. Gate Charge Characteristics

RATINGS AND CHARACTERISTIC CURVES

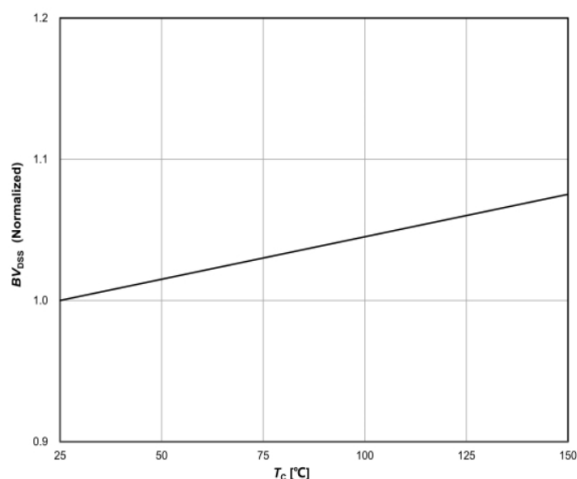


Figure 7. Breakdown Voltage Variation vs Temperature

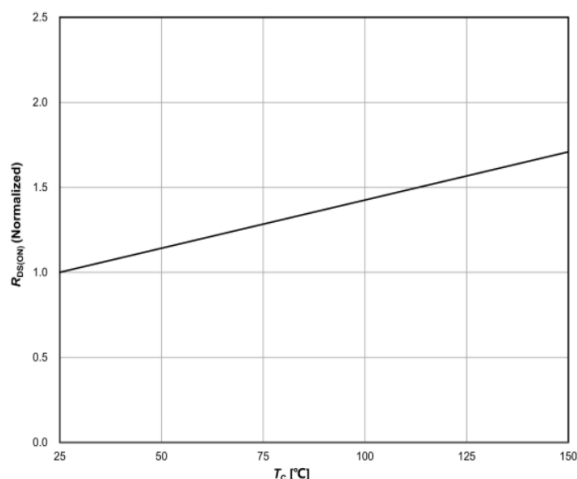


Figure 8. On-Resistance Variation vs Temperature

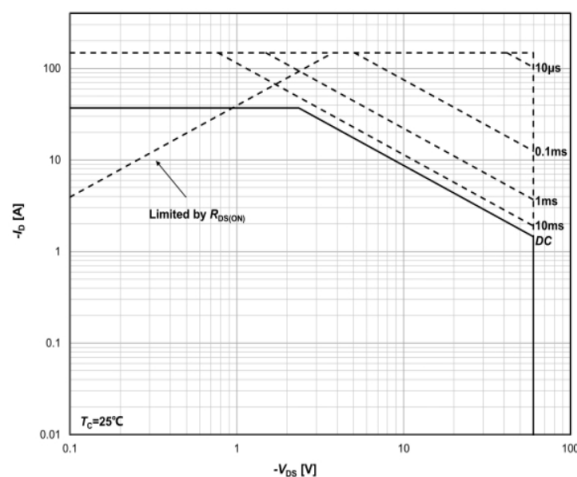


Figure 9. Maximum Safe Operating Area³⁾

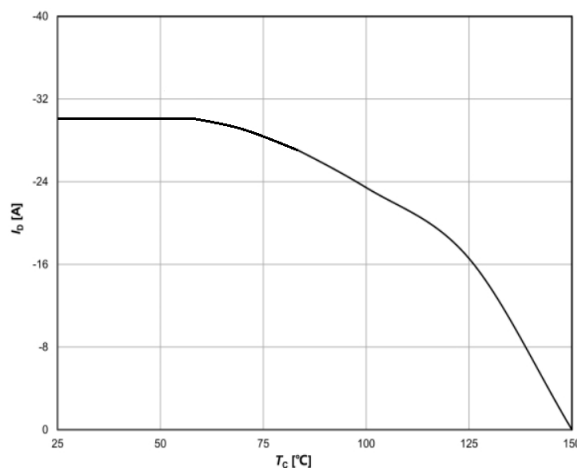


Figure 10. Maximum Drain Current vs Case Temperature

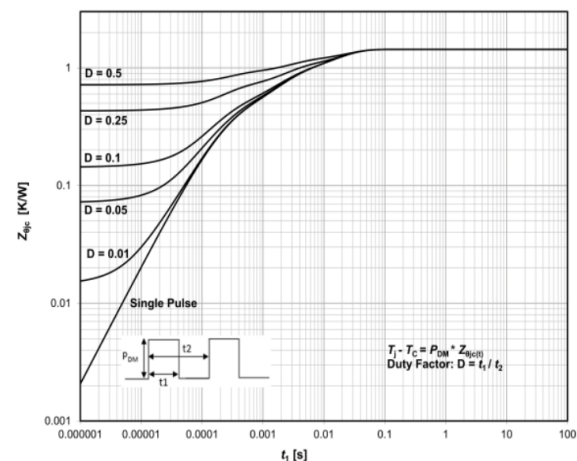
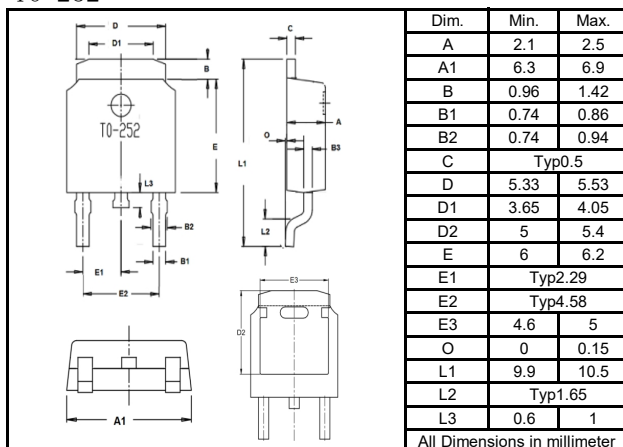


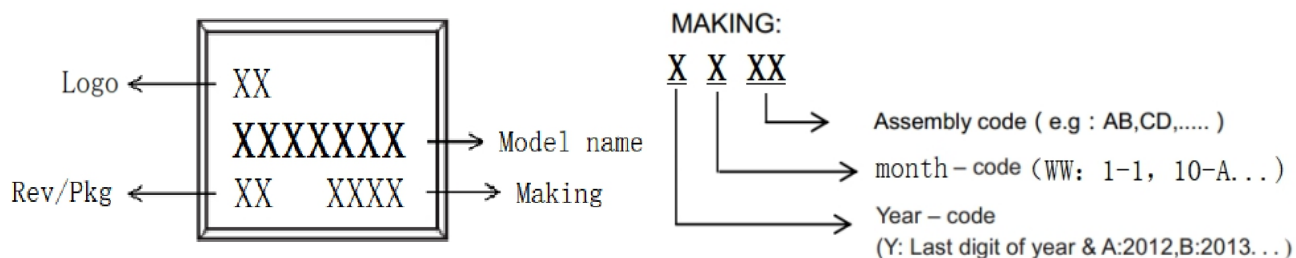
Figure 11. Transient Thermal Response Curve

Package Outline Dimensions millimeters

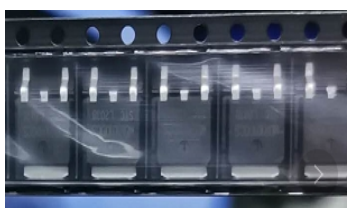
TO-252



Marking on the body



packing instruction

PKG	Minimal Package	Mini Box	Box
TO-252			
	2500pcs/disk	5000pcs/disk	25000pcs/box



LT30P06AD

P-Channel Trench Power MOSFET

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

<http://www.lxmicro.com>

Revision History

Rev	Changes	Date
1.0	First version	2025/6/9